Silicon NPN Power Transistors BU408

DESCRIPTION

·With TO-220C package
·High voltage
·Fast switching speed

APPLICATIONS

·For use in horizontal deflection output stages of TV's and CTV's circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

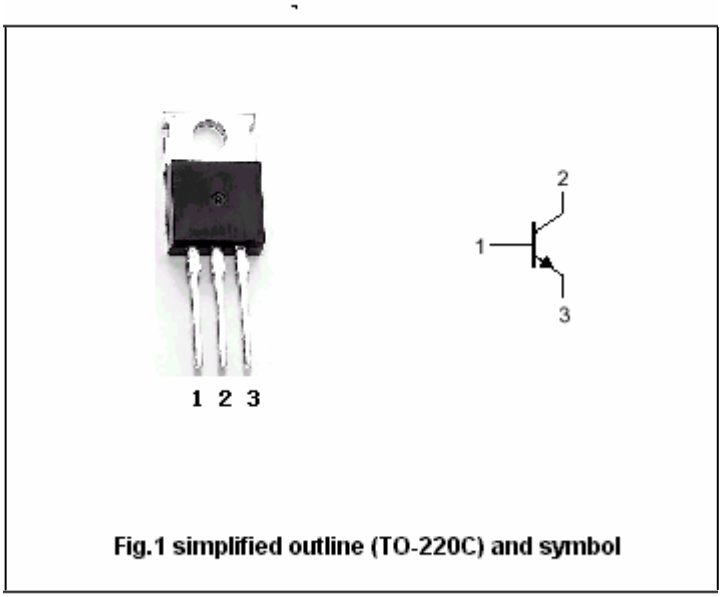

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	400	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		7	A
I_{CM}	Collector current (Pulse)		10	A
I_B	Base current		4	A
P_C	Collector power dissipation	T_C=25□	60	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55-150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ; I_B=0	200			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=6A; I_B=1.2A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=6A; I_B=1.2A			1.5	V
h_{FE}	DC current gain	I_C=2A ; V_{CE}=5V	40			
I_{CES}	Collector cut-off current	V_{CE}=250V; V_{BE}=0 T_C=150□			0.1 1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			1	mA
f_T	Transition frequency	I_C=0.5A ; V_{CE}=10V	10			MHz
t_{off}	Turn-off time	I_C=6A ; I_B=1.2A			0.4	μs

PACKAGE OUTLINE

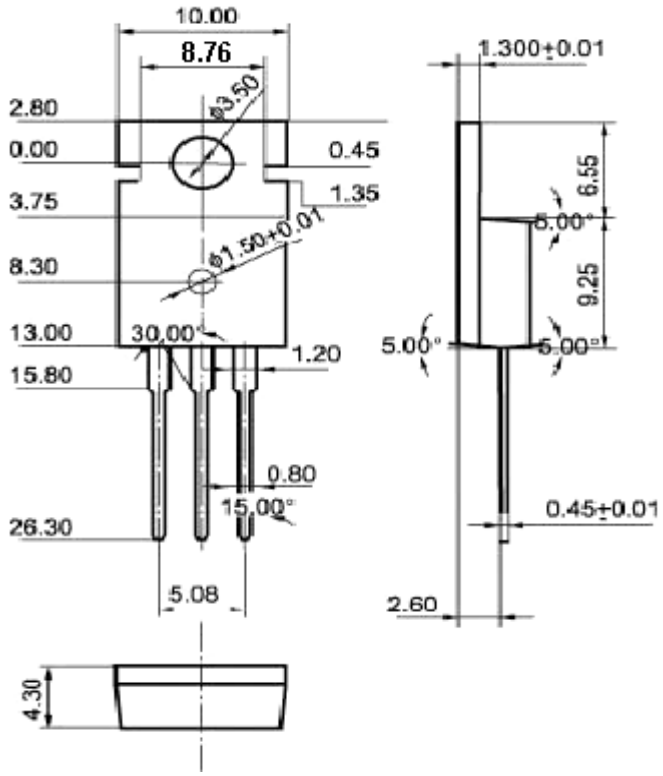

Fig.2 Outline dimensions (unindicated tolerance: ±0.10mm)